



<b>Course: M.Tech. (Electronics &amp; Communication Engineering)</b>	<b>Name of Faculty: Dr.Nalesh S</b>
<b>Topic: 20-437-0105 VLSI Technology &amp; Design</b>	<b>Semester: FIRST</b>
<b>Lecture Hall:</b>	<b>Timings: as per CBCS</b>

<i>Week and date</i>	<i>Lecture topics</i>	<i>Assignments</i>	<i>Remarks</i>
Week 1 (23 <sup>rd</sup> Nov 20)	<b>Module 1: Introduction to CMOS VLSI</b> MOS transistor Ideal I-V characteristics, NMOS Inverter Circuits and Analysis, Complementary MOS Logic - Inverter, Combinational Logic, NAND/NOR gates, CMOS Fabrication Process -FEOL and BEOL processes		
Week 2 (30 <sup>th</sup> Nov 20)	<b>Module 2: Combinational Circuit Design</b> MOSFET capacitances and resistances, Static CMOS Inverter, Static Analysis, Noise Margin	<b>Class Test-1</b> <b>Research Topic Selection for Presentation</b>	
Week 3 (7 <sup>th</sup> Dec 20)	Static CMOS inverter transient response, MOSFET resistance and capacitance, Switching model, Intrinsic Delay, Delay and Sizing	<b>Class Test-2</b>	
<b>APSYM 2020</b>			
Week 4 (17 <sup>th</sup> to 22 <sup>nd</sup> Dec 20)	Chain of inverters, Sizing chain of inverters for optimum delay, Power dissipation in static CMOS inverters		
<b>XMAS Vacations</b>			
Week 5 (29 <sup>th</sup> Dec 20)	Complementary CMOS design -Pull up and Pull Down Networks, Static behavior, VTC Dynamic behavior, Delay dependence on Fanin and Fanout, Sizing of Complementary CMOS gates	<b>Class Test-3</b>	
Week 6 (4 <sup>th</sup> Jan 21)	Logical Effort, Electrical Effort, Stage Effort, Intrinsic Delay, Sizing an chain of gates. Delay of chain of gates, Critical Path	<b>Class Test-4</b>	
Week 7 (11 <sup>th</sup> Jan 21)	Ratioed Logic, Pass-Transistor Logic, Transmission gates, Dynamic Logic, Static Latches and Registers, Dynamic Latches and Registers	<b>Class Test-5</b>	
Week 8 (18 <sup>th</sup> Jan 21)	<b>Module 3: Sequential Circuit Design</b> Timing Metrics- Setup Time, Hold Time, Propagation Delay, Contamination delay, skew and jitter, Setup and Hold violations	<b>Research Topic 1<sup>st</sup> Presentation</b>	
Week 9 (25 <sup>th</sup> Jan 21)	Classification of Memory Elements, Static Latches and Registers, Dynamic Latches and Registers, Pipelining, Memory Cells	<b>Class Test-6</b>	
<b>First Internal Exam</b>			

Week 10 (1 <sup>st</sup> to 12 <sup>th</sup> Feb 21)	<b>Module 5: CMOS Scaling and Sub-Micron Trends:</b> Propagation Delays, Logic and Interconnect delays,		
Week 11 (15 <sup>th</sup> Feb 21)	<b>Module 4: VLSI Design Flow</b> Custom, Semicustom and Structured-Array Design Approaches, Cell Based Design Methodology, Semicustom Design Flow - Design Capture, Register Transfer Logic, Functional Simulation,	<b>Class Test-7</b>	
Week 12 (22 <sup>nd</sup> Feb 21)	High Level Synthesis, Logic Synthesis, Timing Simulation, Static Timing Analysis, Power Analysis, Planning, Partitioning, Placement and Routing, Extraction, Packaging, IC testing		
Week 13 (1 <sup>st</sup> Mar 21)	<b>Module 1: Introduction to CMOS VLSI</b> Introduction, Semiconductors, Band Diagrams, Fermi Level, Intrinsic Semiconductor, Doping, P and N type	<b>Class Test-8</b>	
Week 14 (8 <sup>th</sup> Mar 21)	Current Transport Mechanisms, PN Junctions, Terminology, Quantitative Analysis, Static Behavior, PN Junction Capacitance,	<b>Class Test-9</b>	
Week 15 (15 <sup>th</sup> Mar 21)	MOS Capacitor, Operating regions, Quantitative Analysis, CV characteristics, MOS transistor Ideal I-V characteristics, MOSFET Non Ideal Effects and characteristics	<b>Class Test-10</b>	
<b>Second Internal Exam</b>			
Week 16 (22 <sup>nd</sup> Mar to 2 <sup>nd</sup> Apr 21)	<b>Module 5: CMOS Scaling and Sub-Micron Trends:</b> Scaling Factors for Device Parameters, Constant field scaling and constant voltage scaling, Challenges going to sub-100 nm MOSFETs		
Week 17 (6 <sup>th</sup> Apr 21)	Multiple gate MOSFETs, FinFETs, Carbon nanotube FET, SpinFET, Nanowire FETs	<b>Research Topic Final Presentation</b>	
Week 18 (12 <sup>th</sup> Apr 21)	<b>Publication of Sessional</b>		